

Amendments to the Claims

1. (*Currently Amended*) A semiconductor device (~~105, 205~~) comprising a silicon-containing semiconductor body (~~110, 210~~) with a surface (~~126, 226~~), which semiconductor body (~~110, 210~~) is provided, near the surface thereof (~~126, 226~~), with a transistor comprising: a gate (~~170, 270~~) situated at the surface (~~126, 226~~) and having a side wall spacer (~~136, 138, 236~~) on either side of the gate, and further comprising, on either side of the gate (~~170, 270~~), a diffusion region (~~180, 182, 280~~) formed in the semiconductor body (~~110, 210~~), at least one diffusion region (~~180, 182, 280~~) being provided at the surface (~~126, 226~~) of the semiconductor body (~~110, 210~~) with a silicide (~~190, 192~~), characterized in that the silicide (~~190, 192~~) extends along the surface (~~126, 226~~) of the semiconductor body (~~110, 210~~) and continues for more than 10 nm under the side wall spacer (~~136, 138, 236~~).
2. (*Currently Amended*) A semiconductor device (~~105, 205~~) as claimed in claim 1, characterized in that the silicide (~~190, 192~~) contains a metal which, in the silicide formed, has a higher diffusion rate than silicon.
3. (*Currently Amended*) A semiconductor device (~~105, 205~~) as claimed in claim 2, characterized in that the metal (~~118~~) is selected from the group comprising nickel (Ni), platinum (Pt) and palladium (Pd) and alloys of these metals.
4. (*Currently Amended*) A semiconductor device (~~105~~) as claimed in claim 1, characterized in that the side wall spacer (~~136, 138~~) is L-shaped and comprises a first portion, which borders on the gate (~~170~~) and extends substantially perpendicularly with respect to the surface (~~126~~) of the semiconductor body (~~110~~), and a second portion which extends along the surface (~~126~~) of the semiconductor body (~~110~~).
5. (*Currently Amended*) A semiconductor device (~~105~~) as claimed in claim 4, characterized in that the second portion of the L-shaped side wall spacer (~~136, 138~~) has a thickness (~~D2~~), measured in a direction perpendicular to the surface (~~126~~) of the

semiconductor body ~~(110)~~, of maximally 40 nm.

6. *(Currently Amended)* A semiconductor device ~~(105, 205)~~ as claimed in claim 1, characterized in that an insulating layer ~~(115, 215)~~ extends in the semiconductor body ~~(110, 210)~~ in a direction parallel to the surface ~~(126, 226)~~ of the semiconductor body ~~(110, 210)~~.

7. *(Currently Amended)* A semiconductor device ~~(105)~~ as claimed in claim 1, characterized in that the semiconductor body ~~(110)~~ comprises a germanium component.

8. *(Currently Amended)* A semiconductor device ~~(105)~~ as claimed in claim 1, characterized in that the semiconductor body ~~(110)~~ comprises a strained-silicon layer.

9. Claims 9-13 *(Cancelled)*